

IN THE CLAIMS

Claims 1-13 (Canceled).

14 (Previously Presented). A process comprising:

forming a recess having a bottom and a wall;
forming an electrically resistive film in the recess to form a heater; and
treating the film to have different electrical conductivity at the bottom and the
wall; and
forming a phase change material over said wall.

15 (Currently Amended). The process according to claim 14, wherein treating
includes implanting the film at a first angle and implanting the polysilicon film at a second angle
different from the first angle.

16 (Previously Presented). The process according to claim 14, wherein treating further
comprises doping the film to form discrete isolated regions.

17 (Previously Presented). The process according to claim 14, before treating, further
comprising:

forming a temporary material in the recess; and
 patterning the temporary material to expose the film.

18 (Previously Presented). The process according to claim 14, before treating, further
comprising:

forming a temporary material in the recess;
 patterning a mask over the temporary material; and
 removing a portion of the temporary material to expose the film.

Claims 19-45 (Canceled).